

Memory Module Specification



KHX2333C9D3T1K2/4GX

4GB (2GB 256M x 64-Bit x 2 pcs.) DDR3-2333MHz CL9 240-Pin DIMM Kit

DESCRIPTION:

Kingston's KHX2333C9D3T1K2/4GX is a kit of two 256M x 64-bit (2GB) DDR3-2333MHz CL9 SDRAM (Synchronous DRAM) memory modules, based on sixteen 128M x 8-bit DDR3 FBGA components per module. Each module kit supports **Intel® XMP** (Extreme Memory Profiles). Total kit capacity is 4GB. Each module has been tested to run at DDR3-2333MHz at a low latency timing of 9-11-9 at 1.65V. The SPDs are programmed to JEDEC standard latency DDR3-1333MHz timing of 9-9-9 at 1.5V. Each 240-pin DIMM uses gold contact fingers and requires +1.5V. The JEDEC standard electrical and mechanical specifications are as follows:

FEATURES:

 \checkmark JEDEC standard 1.5V \pm 0.075V Power Supply

 \checkmark VDDQ = 1.5V ± 0.075V

✓ 667MHz fCK for 1333Mb/sec/pin

8 independent internal bank

Programmable CAS Latency: 6,7,8,9

Posted CAS

Programmable Additive Latency: 0, CL - 2, or CL - 1 clock

Programmable CAS Write Latency(CWL) = 7(DDR3-1333)

8-bit pre-fetch

Burst Length: 8 (Interleave without any limit, sequential with starting address "000" only), 4 with tCCD = 4 which does not allow seamless read or write [either on the fly using A12 or MRS]

Bi-directional Differential Data Strobe

Internal(self) calibration: Internal self calibration through ZQ pin (RZQ : 240 ohm \pm 1%)

On Die Termination using ODT pin

Average Refresh Period 7.8us at lower then TCASE 85°C, 3.9us at 85°C < TCASE . 95°C

Asynchronous Reset

PCB: Height 2.401" (61.00mm) w/ heatsink, double sided component

PERFORMANCE:

CL(IDD)

Row Cycle Time (tRCmin)

Refresh to Active/Refresh Command Time (tRFCmin)

Row Active Time (tRASmin)

Power

UL Rating

Operating Temperature

Storage Temperature

9 cycles

49.5ns (min.)

110ns

36ns (min.)

1.800 W (operating per module)

94 V - 0

0° C to 85° C

-55° C to +100° C

MODULE DIMENSIONS:





